

Low Profile 4 Mbit/s (FIR) Infrared Transceiver Module with Independent Logic Supply Voltage

Description

The Vishay TFBS6614 is the lowest profile (2.7 mm) 4 Mbit/s Infrared Data Transceiver module available. A photo PIN diode, an infrared emitter (IRED) and a low-power CMOS control IC are integrated in a single package that provides a total front-end solution.

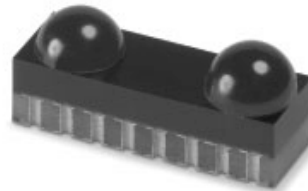
V_{LOGIC} - allows a low-voltage controller to connect directly to TxD, RxD and SD/Mode logic signals of the transceiver hence eliminating the need for costly signal level converter and reducing power consumption.

The TxD-echo function is enabled for internal self-test. During transmission the TxD signals are echoed at RxD output to perform the internal self-test.

The Shut Down (SD) feature cuts current consumption to less than 10 nA.

Features

- Smallest FIR Transceiver available:
H 2.7 mm x D 3.33 mm x L 7.98 mm
- 1.0 m Link distance
- Battery & Power Management Features:
 - > Receive - 2 mA Typical
 - > Shutdown - 10 nA Typical
 - > Independent LED Anode Power Supply
 - > Wide Voltage Range 2.7 V - 5.5 V
 - > Power Up Latency < 100 μ s
 - > High V_{CC} Noise Rejection > 100 m VPP
- The TxD-Echo function is enabled
- V_{LOGIC} (1.5 V - 5.5 V) - Independent Digital supply voltage
- Shutdown Tri-States Receiver Output and Disables TxD allowing Bus Interfacing
- High Immunity to Fluorescent Light Noise and AC Field. No external shield required



- High DC Ambient Rejection - Operates Outdoors
- Receiver Latency Less than 100 μ s
- Directly Interfaces with Various Super I/O and Controller Devices

Applications

PDA's
 Mobile Phones
 Notebook Computers, Desktop PCs
 Digital Still and Video Cameras
 External Infrared Adapters (Dongles)
 Diagnostics Systems
 Medical and Industrial Data Collection Devices
 GPS

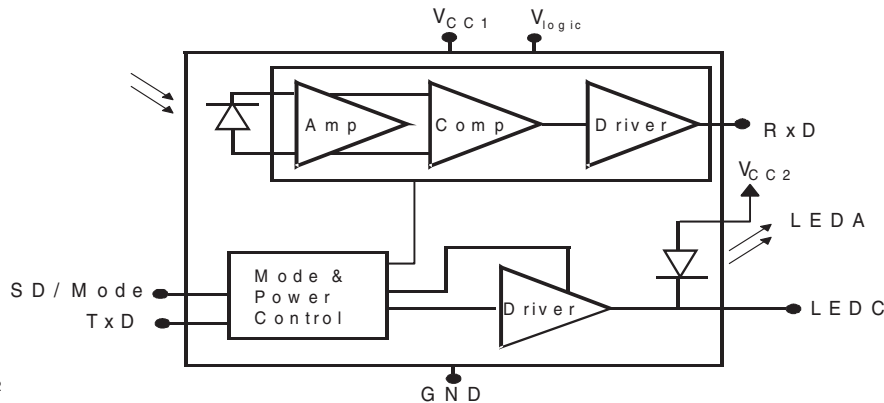
Footnotes

Product Disclaimer
 This product is under development. Specifications are subject to change.

Parts Table

Part	Description	Qty / Reel
TFBS6614-TR3	Oriented in carrier tape for side view surface mounting	2500 pcs

Functional Block Diagram



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Pin Description

Pin Number	Function	Description	I/O	Active
1	V_{CC2} , IRED Anode	Connect IRED Anode directly to V_{CC} . To decrease the LED current add a resistor between V_{CC} and IRED Anode. A non-regulated separate power supply can be used at this pin.		
2	IRED Cathode	IRED Cathode, internally connected to driver transistor		
3	TxD	Transmit Data Input	I	HIGH
4	RxD	Received Data Output, capable of driving a standard CMOS or TTL load. No external pull-up or pull-down resistor is required. Pin is floating when device is in shutdown mode and is not quiet during data transmission.	O	LOW
5	SD/ Mode	Places the device in shutdown mode and switches bandwidth together with Tx D	I	HIGH
6	V_{CC1}	Analog Supply Voltage		
7	V_{LOGIC}	Digital Supply Voltage		
8	GND	Ground		

Absolute Maximum Ratings

Reference Point Ground, Pin 8, unless otherwise noted

Parameter	Testconditions	Symbol	Value	Unit
Analog Supply Voltage Range, all states		V_{CC1}	- 0.5 to 6.0	V
Digital Supply Voltage Range		V_{DD}	- 0.5 to 6.0	V
Input Current	During Transmit, $V_{CC} = 5.0$ V, Tx D = V_{DD}		10.0	mA
Output Sink Current, Rx D			25.0	mA
Peak IRED Current	$V_{CC1} = 2.7$ V, Tx D = V_{DD} , 125 ns pulse		650	mA
Average IRED Current	$V_{CC2} = 2.7$ V		125	mA
Power Dissipation			500	mW
Junction Temperature			125	°C
Ambient Temperature Range (Operating)		T_A	- 25 to + 85	°C
Storage Temperature Range		T_S	- 25 to + 85	°C
Soldering Temperature	$t = 20$ s @ 215 °C		215 (≤ 240)	°C
Transmitter Data and Shutdown Input Voltage		V_{TxD}, V_{SD}	- 0.5 to $V_{DD} + 0.5$	V
Receiver Data Output Voltage		RxD	- 0.5 to $V_{DD} + 0.5$	V

Optoelectronic Characteristics

Receiver

$T_A = 25\text{ }^\circ\text{C}$, $V_{CC} = 2.7\text{ V}$ to 5.5 V unless otherwise noted

Parameter	Testconditions	Symbol	Min	Typ.	Max	Unit
Minimum Detection Threshold Irradiance	4.0 Mbits/s, $\lambda = 850\text{ nm}$ to 900 nm	E_e			100	mW/m^2
Analog Supply Voltage Range	Specified operation	V_{CC}	2.7		5.5	V
Digital Supply Voltage Range	Specified operation	V_{DD}	1.5		5.5	V
Maximum LED Anode Voltage		V_{LEDA}			$V_{CC} + 4$	V
I_{CC} Shut Down Current	$V_{CC} = 5\text{ V}$	I_{CC1}		0.01	2.0	nA
I_{CC} Idle Current	$V_{CC} = 5\text{ V}$	I_{CC2}		1.6		mA

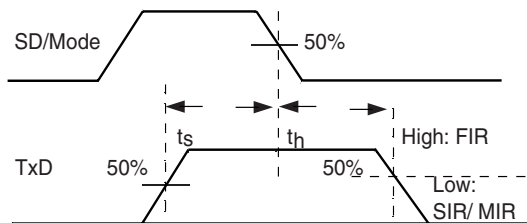
Transmitter

$T_A = 25\text{ }^\circ\text{C}$, $V_{CC} = 2.7\text{ V}$ to 5.5 V unless otherwise noted

Parameter	Testconditions	Symbol	Min	Typ.	Max	Unit
Output Radiant Intensity	$\alpha = 0\text{ }^\circ\text{C}$, $15\text{ }^\circ\text{C}$, TxD = High, SD = Low	I_e		110		mW/Sr

Mode Switching

Upon power-up the TFBS6614 module initializes in the SIR (9.6 Kbit/s to 115.2 Kbit/s) mode. The module can be switched to higher bandwidth and vice versa by using the sequence described below:



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Setting to the High Bandwidth Mode (0.576 Mbits/s to 4 Mbit/s)

1. Set SD/ Mode input to logic "High".
2. Set TxD input to logic "High". Wait $t_s \geq 200\text{ ns}$.
3. Set SD/ Mode to logic "Low" (the negative edge latches state of TxD, which determines data rate setting).
4. After waiting $t_h \geq 200\text{ ns}$ TxD can be set to logic "Low". The hold time of TxD is limited by the maximum allowed pulse width.

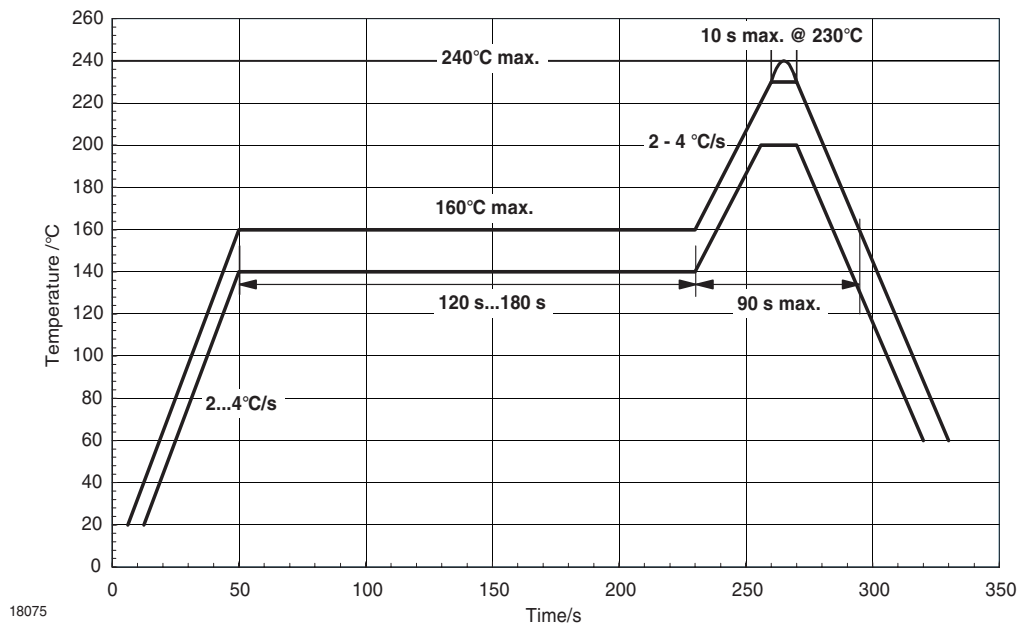
TxD is now enabled as normal TxD input for the high bandwidth mode.

Setting to the Lower Bandwidth Mode (9.6 Kbit/s to 115.2 Kbit/s)

1. Set SD/ Mode input to logic "High".
2. Set TxD input to logic "Low". Wait $t_s \geq 200\text{ ns}$.
3. Set SD/ Mode to logic "Low" (the negative edge latches state of TxD, which determines data rate setting).
4. After waiting $t_h \geq 200\text{ ns}$ TxD can be set to logic "Low". The hold time of TxD is limited by the maximum allowed pulse width.

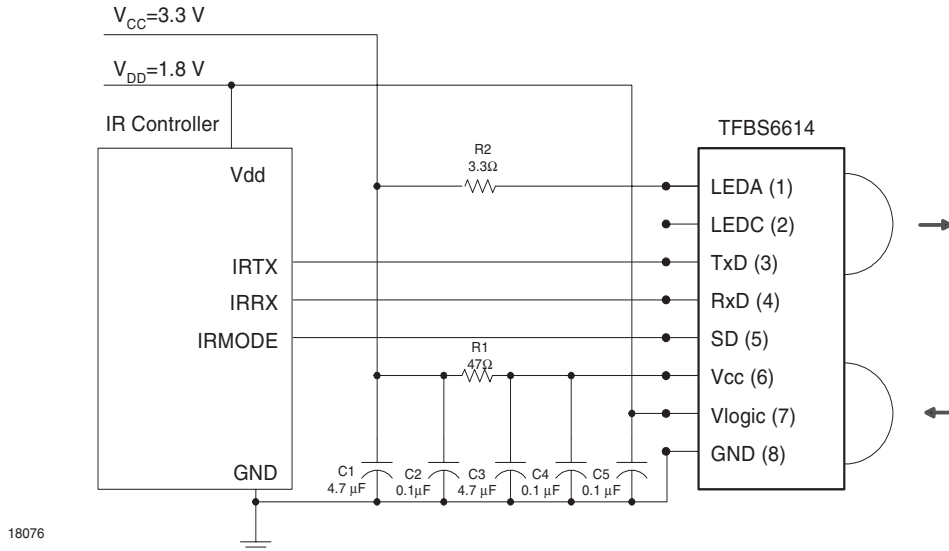
TxD is now enabled as normal TxD input for the lower bandwidth mode.

Recommended Solder Profile



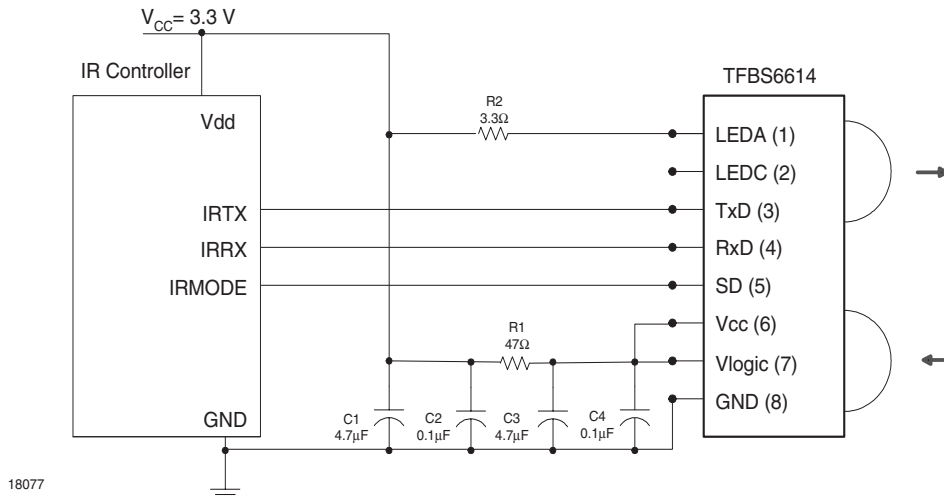
Recommended Circuits

Block Diagram of Transceiver with Digital Power Supply



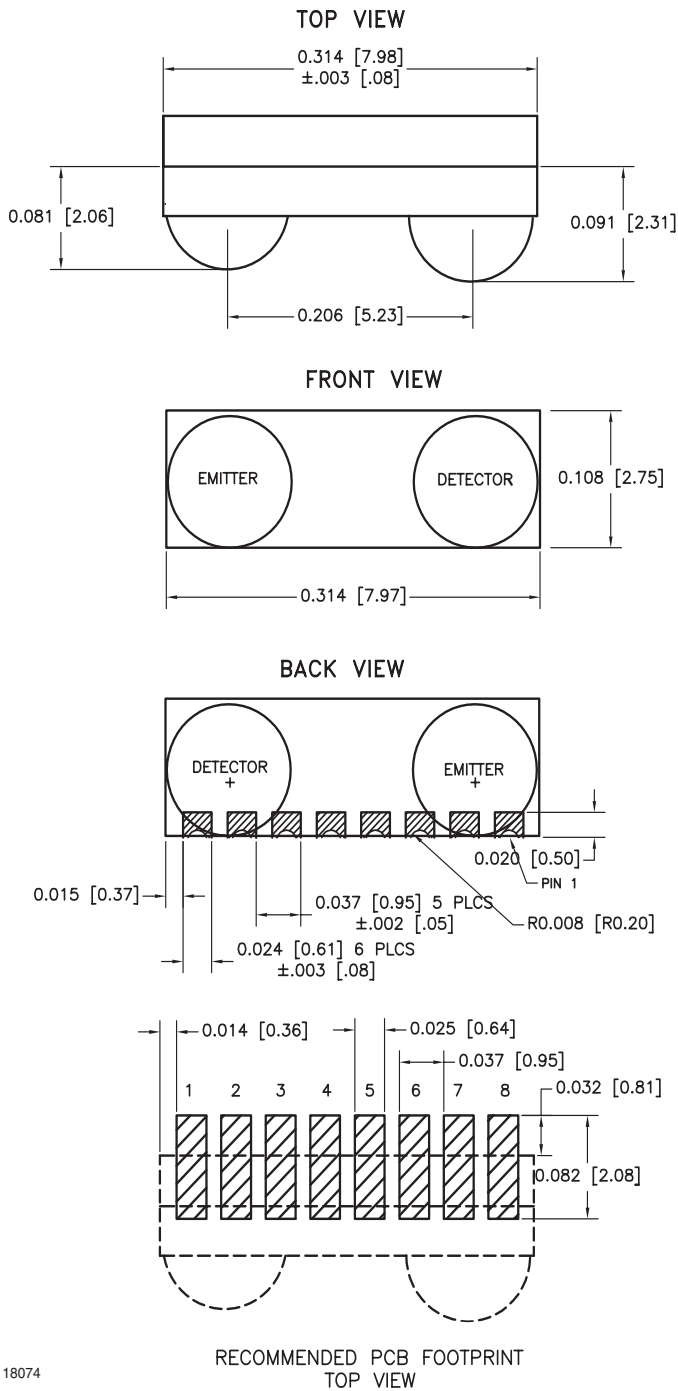
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Block Diagram of Transceiver with Common Power Supply



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Package Dimensions in Inches (mm)



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Ozone Depleting Substances Policy Statement

It is the policy of **Vishay Semiconductor GmbH** to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

**We reserve the right to make changes to improve technical design
and may do so without further notice.**

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay Semiconductors products for any unintended or unauthorized application, the buyer shall indemnify Vishay Semiconductors against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

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